Abstracts

2.5-Watt and 5-Watt Internally Matched GaAs FETs for 10.7-11.7 and 14-14.5 GHz Bands

M. Avasarala and D.-Y.S. Day. "2.5-Watt and 5-Watt Internally Matched GaAs FETs for 10.7-11.7 and 14-14.5 GHz Bands." 1986 MTT-S International Microwave Symposium Digest 86.1 (1986 [MWSYM]): 455-458.

A new 7.2mm GaAs FET chip with high gain, power, efficiency and low thermal resistance has been developed. Internally matched packaged devices using one and two such FETs have been developed for the 10.7-11.7 and 14-14.5GHz bands. At 11.7GHz the 7.2mm and 14.4mm devices have achieved power gain, and power-added-efficiency of 35.3dBm, 8dB, 33% and 37.8dBm, 8.0dB and 31.5% respectively at the 1dB gain compression point. At 14.5GHz the results are 34dBm, 7dB, 25% and 37.0dBm, 6dB and 18.5% respectively at the 1dB gain compression point.

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